Solution-Processed Squaraine Bulk Heterojunction Photovoltaic Cells

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ulk-heterojunction (BHJ) solar cells based on interpenetrating blends of electron- and hole-transporting materials offer promise for low-cost, sustainable, electricity production.^{1–3} Efficient charge generation throughout the active blends, ultrafast charge transfer at the donor/acceptor interface, and efficient charge transport are essential for high performance photovoltaic applications.⁴ Because of the potentially low-cost of fabrication, solution processing has been widely explored to demonstrate polymeric bulk solar cells with high power efficiencies,^{5–7} although the dependence of performance on polymer materials such as regioregularity, polydispersity, and stability⁸ have not been fully addressed.

In contrast, small molecules are intrinsically monodisperse and simple to synthesize and purify. In general, the concept of the bulk heterojunction has been demonstrated in small-molecular weight organic solar cells with active layers codeposited by vacuum thermal evaporation⁹ or organic vapor phase deposition.¹⁰ There are also examples of small molecules that have been used as solution processable donor materials in BHJ architectures.^{11–13} Unfortunately, the strong intermolecular forces between conjugated small molecules can result in the nucleation of molecular crystals in solution, generating incomplete film coverage with high surface roughness in such BHJs. To obtain improved performance, efforts have focused on the design and synthesis of soluable donors with high charge carrier mobility and absorption in the visible and new-infrared spectral regions, in combination with a high interfacial gap energy at the donor-acceptor interface.⁸ Among these, 2,4-bis[4-(N,N-diisobutylamino)-2,6dihydroxyphenyl] squaraine (SQ) dyes with

ABSTRACT The donor, 2,4-bis[4-(*N*,*N*-diisobutylamino)-2,6-dihydroxyphenyl] squaraine (SQ) is used with the acceptor, [6,6]-phenyl C₇₀ butyric acid methyl ester (PC₇₀BM) to result in efficient, solution-processed, small-molecule bulk heterojunction photovoltaic cells. The distribution of the donor nanoparticles in the acceptor matrix as a function of relative concentrations results in a trade-off between exciton dissociation and hole mobility (and hence, cell series resistance). A bulk heterojunction solar cell consisting of an active region with a component ratio of SQ to PC₇₀BM of 1:6 has a power conversion efficiency of 2.7 ± 0.1% with a 8.85 ± 0.22 mA/cm² short-circuit current density and an open-circuit voltage of 0.89 ± 0.01 V obtained under simulated 1 sun (100 mW/cm²) air mass 1.5 global (AM1.5 G) solar illumination. This is a decrease from 3.3 ± 0.3% at 0.2 sun intensity, and is less than that of a control planar heterojunction SQ/C₆₀ cell with 4.1 ± 0.2% at 1 sun, suggesting that the nanoparticle morphology introduces internal resistance into the solution-based thin film. The nanomorphology and hole mobility in the films is strongly dependent on the SQ-to-PC₇₀BM ratio, increasing by greater than 2 orders of magnitude as the ratio increases from 28% to 100% SQ.

KEYWORDS: solar cell · photovoltaic · bulk heterojunction · small molecule · solution processing

hydroxyl groups at the 2,6-positions of the two phenyl rings¹⁴ have been identified as donors that absorb at wavelengths $\lambda > 650$ nm which, when combined with a C₆₀ acceptor layer, have a larger open circuit voltage (*V*_{oc}) than that of the commonly used copper phthalocyanine (CuPc)/C₆₀ cell.¹⁵ This particular squaraine is attractive since the addition of the four hydroxyl groups gives the compound added stability over alternative formulations and it can be vacuum sublimed without decomposition.

In this paper, we show that the combination of the optical, electrical, and chemical properties of SQ blended in solution with [6,6]-phenyl C₇₀ butyric acid methyl ester (PC₇₀BM) in a 1:6 mixture results in cells with power conversion efficiency $\eta_p = 2.7 \pm 0.1\%$, short-circuit current density $J_{sc} = 8.85 \pm 0.22$ mA/cm², and $V_{oc} = 0.89 \pm 0.01$ V at 1 sun intensity, AM1.5G simulated solar emission, and a peak external quantum efficiency EQE = 48% at a wavelength of λ = 385 nm. Its peak $\eta_p = 3.3 \pm 0.3\%$ at 0.2

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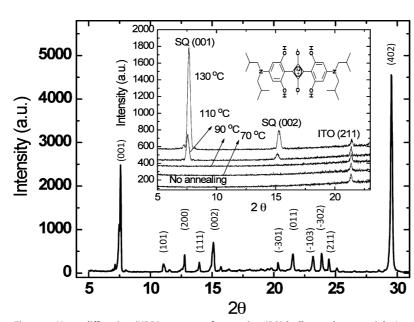


Figure 1. X-ray-diffraction (XRD) patterns of squaraine (SQ) bulk powder materials. Inset: SQ thin film spin-coated from dichloromethane solvent on indium tin oxide (ITO) coated glass substrates. The diffraction peaks are indexed using Winplotr and FullProf^{17,18} software routines. XRD spectra indicate that the neat SQ film annealed at 110 and 130 °C has the same crystal structure as the powder, with the (001) and (002) crystal axes normal to the substrate plane. No peaks are found for any of the SQ:PC₇₀BM blended films, indicating that they are amorphous. Also shown in the inset is the molecular structural formula of SQ.

sun is compared with a control, planar heterojunction SQ/C_{60} cell with an efficiency of 4.1 \pm 0.2% at 1 sun (correcting for solar mismatch). We show that the morphology of the SQ:PC₇₀BM composites affects the hole transport mobility, resulting in an unbalanced electron and hole transport and relatively low fill factor (FF). The higher efficiency of the control SQ/C₆₀ device is due to the nanocrystalline interdigitated bilayer morphology, resulting in high hole mobility and hence efficient charge collection efficiency.

RESULTS

The molecular structural formula (inset of Figure 1) for the SQ contains two phenyl rings with four hydroxyl groups that result in its solubility.¹⁴ Its thermal properties have been previously reported,¹⁶ with a melting point of 294 °C and a deposition temperature of 299 °C. The SQ powder characterized by XRD (Figure 1) indicates a monoclinic unit cell [space group *P2/m* with a = 14.95, b = 9.35, c = 11.50 Å, $\beta = 98.20^\circ$].^{17,18} Thin films annealed at 110 and 130 °C for 10 min exhibit (001) and (002) peaks at $2\theta = 7.58^\circ$ and $2\theta = 15.29^\circ$ (inset, Figure 1) corresponding to an intermolecular spacing of $d_{002} = 5.75$ Å. There are no peaks for SQ, PC₇₀BM, and SQ:PC₇₀BM blends with five different ratios of 3:1, 1:1, 1:2, 1:3, and 1:6 annealed at 70 °C, indicating amorphous films.

The absorption spectra of pure SQ and blends of SQ: PC₇₀BM films annealed at 70 °C on quartz substrates are shown in Figure 2. The SQ absorption extends to wavelengths of $\lambda = 750$ nm with a peak at $\lambda = 680$ nm. When mixed with PC₇₀BM with absorptions centered at λ = 375 and λ = 465 nm, the resulting film has coverage across the visible spectrum. As the fraction of PC₇₀BM increases, the SQ absorption peak is suppressed, with a concomitant increase in absorption from λ = 300 to λ = 500 nm, characteristic of PC₇₀BM.

In Figure 3, inset, we plot the J-V characterisitcs of a hole-only device with a 1:1 SQ: PC₇₀BM blend, with the top cathode biased positive with respect to the anode. The data follow $J \propto V$,² and hence are fit to a trap-free space charge limited model¹⁹ to extract the zero-field hole mobility (μ_0) as shown. Here, μ_0 decreases from 1 \times 10⁻⁵ to 1.2 \times 10⁻⁷ cm²/(V s) when the molecular weight percentage of SQ decreases from 100% (pure SQ

thin films) to 28%. A minimum of 4×10^{-8} cm²/(V s) is obtained for a 1:3 mixture (corresponding to 42 wt % SQ in PC₇₀BM). With the exception of the 100% SQ control device, the lowest mobility is obtained for the roughest films. Indeed, in the mixed films, we show later that the hole mobility along discontinuous conduction pathways limits cell performance in contrast to electron mobility in PC₇₀BM.

The EQE (Figure 4) and J-V (Figure 5) characteristics of the blended and control solar cells are summarized in Table 1. The addition of PC₇₀BM broadens the spectral response of the cells into the wavelength range from $\lambda = 450$ to 600 nm. The 3:1 and 1:1 blend film devices show EQE < 22% at the absorption peak of SQ, in-

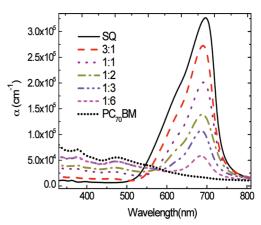


Figure 2. The absorption coefficient (α) of pure squaraine, PC₇₀BM, and blends of both materials on quartz substrate with SQ:PC₇₀BM ratios of 3:1, 1:1, 1:2, 1:3, and 1:6.

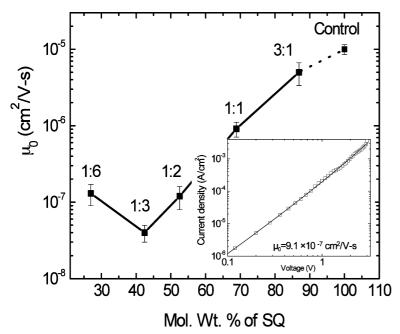


Figure 3. The zero-field hole hole mobility (μ_0) *versus* molecular weight ratio between squaraine and PC₇₀BM. Inset: Typical current density *vs* voltage characteristic of samples used for mobility measurement. A fit to the data (straight line) gives $\mu_0 = 9.1 \times 10^{-7} \text{ cm}^2/(\text{V s})$ for a SQ:PC₇₀BM 1:1 blend.

creasing to 48% at $\lambda = 385$ nm (due to PC₇₀BM) for a 1:6 mixture. Comparison with the absorption characteristics in Figure 2 indicate that the relative balance between the EQE due to SQ and PC₇₀BM absorption in the mixed cells suggests that charge collection, and not exciton dissociation, governs cell performance.

In Figure 5, we show the J-V characteristics at very low (Figure 5a) and at 1 sun intensity (Figure 5b) AM1.5G illumination. At the higher intensities, we find

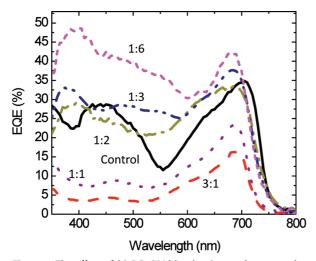


Figure 4. The effect of SQ:PC₇₀BM blend ratios on the external quantum efficiency (EQE) for the five bulk cells with a device structure of ITO/MoO₃(80 Å)/SQ:PC₇₀BM(x Å)/Al(1000 Å), and the EQE of the SQ/C₆₀ planar control cell with a device structure of ITO/MoO₃(80 Å)/SQ(62 Å)/C₆₀(400 Å)/bathocuproine (BCP)(100 Å)/Al(1000 Å). Here, x = 320, 400, 720, 730, and 760 Å for the five blend cells with compositions 3:1, 1:1, 1:2, 1:3 and 1:6, respectively.

that V_{oc} ranges from 0.75 to 0.90 V as shown in Figure 6a, with the higher values corresponding to cells with a low FF. Hence, the largest open circuit voltages are due, in part to the higher resistance of the cells. Nevertheless, these V_{oc} are consistently higher than previously reported 0.62 V for the SQ:PC₆₀BM bulk cells,¹¹ as a result of the lower saturation dark current, J_0 , of our MoO₃ based cells (see Table 1).

The fill factors and power conversion efficiencies of the solution-processed solar cells are shown in Figures 6b and 7, respectively. The incorporation of a MoO₃ buffer layer leads to a reduction in dark current arising from electron leakage to the anode²⁰ and hence a concomitant increase in V_{oc} . The SQ/C₆₀ control cells have the highest fill factor of FF = 0.54 ± 0.02 at 1 sun inten-

sity, compared to FF = 0.26 to 0.35 for the SQ:PC₇₀BM cells (Table 1). Because of the low fill factor, the power conversion efficiency of the 1:6 SQ:PC₇₀BM cell drops from 3.0 \pm 0.3% with FF = 0.38 \pm 0.01 at 0.2 sun (20 mW/cm²) AM1.5G illumination, to η_p = 2.7 \pm 0.1% with FF = 0.35 \pm 0.01 at 1 sun. This is comparable to the SQ/C₇₀ planar cell, with η_p = 2.7 \pm 0.1%, V_{oc} = 0.72 \pm 0.01 V, and FF = 0.45 \pm 0.02 under similar illumination conditions. It is notable that the performance of both

the 1:6 SQ:PC₇₀BM and SQ:PC₆₀BM cells are qualitatively similar, as apparent in Table 1. The somewhat reduced V_{oc} of the latter cell is due to the comparatively large $J_0 = 1.6 \times 10^{-5}$ mA/cm², vs 6.2×10^{-7} mA/cm² for the PC₇₀BM-based cell.

The highest efficiencies achieved are with the 1:2 blended films at low illumination intensity and the planar SQ/C₆₀ control device at 1 sun intensity, both peaking at 4.1 \pm 0.2%. Note that introducing a bathocuproine blocking layer between the cathode and C₆₀, as is typical of high performance planar junction cells,¹⁰ reduces the efficiency to 2.7% in the control cell. As in the case of the 1:6 blended cell, the 1:2 cell efficiency falls off sharply with light intensity, along with a concomitant decrease in FF. In contrast, the unblended, planar control with its relatively high and intensity-independent FF shows only a weak efficiency dependence as intensity is varied from 0.01 to 2 suns.

DISCUSSION

Examination of the AFM images of the pure SQ, pure $PC_{70}BM$ and their blended films as deposited

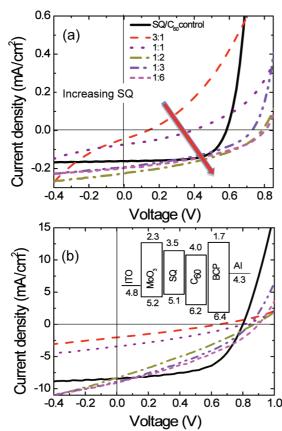


Figure 5. Current density–voltage (J-V) characteristics illuminated at (a) 0.02 sun; (b) 1 sun for the SQ:PC₇₀BM blended bulk cells, and the SQ/C₆₀ planar control cell. Inset shows the energy level diagram of the SQ:C₆₀ control cell.

on 80 Å thick MoO₃ buffer layers shown in Figure 8 suggest that film nanomorphology largely controls the cell performance and the hole mobility (Figure 3). While the pure, nanocrystalline SQ film in Figure 8c has a root-mean-square (rms) roughness of 1.7 ± 0.02 nm, those containing neat PC₇₀BM are very smooth with a rms roughness of only 0.55 ± 0.04 nm (Figure 8a). The active layer roughness of five blends for the ratios of 3:1, 1:1, 1:2, 1:3. and 1:6 are plotted in Figure 8d, and indicate a surface sufficiently smooth to fabricate devices with films free of pinholes and other macroscopic defects. At the highest SQ concentrations, the decreased roughness of <0.8 nm indicates amorphous SQ clusters that are likely separated by intervening PC₇₀BM. The

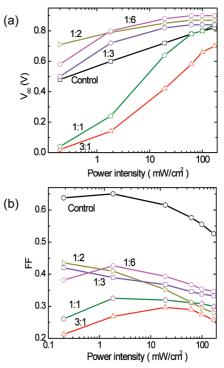


Figure 6. (a) Open circuit voltage (V_{oc}), and (b) fill factor (FF) as functions of AM1.5G spectral illumination power (corrected for solar spectral mismatch) of the five blended SQ: PC₇₀BM cells and the squaraine/C₆₀ planar control cell.

separate domains of SQ in a matrix of PC₇₀BM are apparent in Figure 8b for a 1:3 SQ:PC₇₀BM blend. The tendency of SQ to aggregate leads to a surface with a roughness of 1.6 \pm 0.1 nm. Note that at this concentration, the hole mobility has a minimum value of 4 \times 10⁻⁸ cm²/(V s), indicating a nonuniform distribution of SQ domains throughout the blend.

The highest efficiencies are achieved for the planar SQ/C_{60} devices, where the SQ is both rough (Figure 8) and crystalline (Figure 1, inset). In this case, the rms roughness of 1.7 nm is characteristic of the crystallite size and is on the order of an exciton diffusion length in such materials.²¹ Hence, the rough interface between SQ and C₆₀ forms a nanocrystalline interdigitated bilayer or BHJ similar to that previously demonstrated between CuPc and C₆₀ grown by organic vapor phase deposition.¹⁰ Note that the considerably lower efficiency obtained for the control SQ/C₇₀ cell than for the

SQ:PC ₇₀ BM ratio	V _{oc} (V)	J _{sc} (mA/cm ²)	FF	J₀ (mA/cm²)	$\eta_{ m P}$ (%) at $P_{ m 0}=$ 1 sun	η _P (%) (max)	P_0 at max η_p (mW/cm ²)
3:1	0.68(±0.03)	1.79(±0.19)	0.26(±0.01)	$2.8 imes10^{-2}$	0.32(±0.01)	0.32(±0.01)	100
1:1	0.81(±0.01)	3.61(±0.03)	0.31(±0.01)	$1.1 imes 10^{-2}$	0.90(±0.01)	0.90(±0.01)	100
1:2	0.87(±0.01)	8.33(±0.50)	0.29(±0.01)	$3.7 imes 10^{-7}$	2.1(±0.1)	4.1(±0.2)	2
1:3	0.84(±0.01)	8.83(±0.34)	0.33(±0.01)	$8.7 imes10^{-6}$	2.4(±0.1)	3.0(±0.1)	2
1:6	0.89(±0.01)	8.85(±0.22)	0.35(±0.01)	$6.2 imes 10^{-7}$	2.7(±0.1)	3.3(±0.1)	20
1:6/BCP	0.84(±0.01)	9.33(±0.12)	0.36(±0.01)	$2.7 imes 10^{-7}$	2.9(±0.2)	3.8(±0.2)	0.2
SQ:PC ₆₀ BM1:6	0.78(±0.01)	9.17(±0.25)	0.42(±0.01)	$1.6 imes10^{-5}$	3.0(±0.1)	3.6(±0.1)	2
SQ/C ₆₀	0.79(±0.01)	8.90(±0.25)	0.54(±0.02)	$1.2 imes10^{-6}$	3.8(±0.2)	4.1(±0.2)	100
SQ/C ₇₀	0.72(±0.01)	8.29(±0.25)	0.45(±0.02)	$1.1 imes 10^{-5}$	2.7(±0.2)	3.1(±0.2)	20

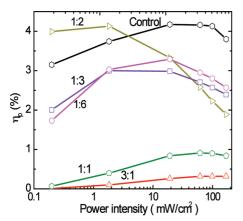


Figure 7. Power conversion efficiency (η_p) as a function of AM1.5G spectral illumination power (corrected for solar spectral mismatch) of the five blended SQ:PC_{70}BM cells and the squaraine/C_{60} planar control cell. The highest efficiencies are 4.1 \pm 0.2% for the control (at 1 sun) and the 1:2 (at 0.02 suns) cells.

 SQ/C_{60} (Table 1) device may be due to lower purity of the C_{70} . This is also apparent from its roll off in efficiency and fill factor at high intensities, indicative of high series resistance.

While exciton dissociation in uniform blends with a high SQ content (*e.g.*, 1:1 and 3:1) is expected to be efficient, the EQE of these devices is low, and the resulting solar cells are inefficient, particularly at light intensities of >0.1 sun. Hence, we infer that the donor—acceptor interfaces in these mixtures often lie beyond a diffusion length of the exciton generation sites. We note, however, that the hole mobility for such mixtures is comparatively high. This suggests that SQ forms continuous conducting pathways for holes between anode and cathode. To test this assumption, we measured the parallel resistances of the PV cells by fitting their dark current *versus* voltage characteristics to the modified Shockley Equation:²²

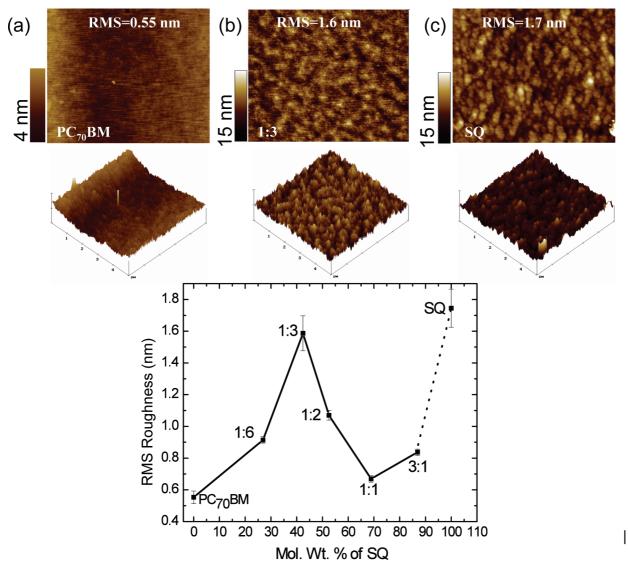


Figure 8. Atomic force microscope topographic and 3D images of (a) pure $PC_{70}BM$, (b) 1:3 SQ: $PC_{70}BM$, and (c) pure SQ films deposited on indium tin oxide coated glass. The field of view of each film is 5 μ m × 5 μ m. (d) The root-mean-square (rms) roughness versus the molecular weight ratio of squaraine blended into $PC_{70}BM$ taken from AFM data as shown in images a – c.

$$J = J_0 \left[\exp \frac{q(V - JR_s)}{nkT} - 1 \right] + \frac{V - JR_s}{R_p}$$

where *q* is the electron charge, *n* is the ideality factor R_s is the diode specific series resistance, and R_p is its specific parallel (or shunt) resistance. The resulting values for J_0 and R_p are shown in Table 1 and Figure 9, respectively, indicating that the films with large concentrations of SQ have a very low parallel resistance, consistent with the existence of shorts formed by percolating hole transport pathways. These pathways also lead to very high J_0 and hence suppressed V_{oc} . Indeed, from the correlation between the increase in *dark current* and R_p , we can rule out field-dependent dissociation of photogenerated geminate electrons and holes at entangled donor—acceptor interfaces as the source of decreased resistance at high SQ content.

Photoelectron spectroscopy measurements indicate an ionization potential energy (IPE) for SQ of 5.1 eV, compared to 6.2 eV for C₆₀ (inset, Figure 5b). Including the energy gap for C_{60} of $E_G(C_{60}) = 2.2 \text{ eV}$, we obtain an interface gap between SQ and C_{60} of 1.1 eV. (Here, the interface energy gap is equal to $\Delta E_{\rm G} =$ $IPE(C_{60}) + E_G(C_{60}) - IPE(SQ)$.) While this is larger than the measured $V_{\rm oc} = 0.9$ V as shown in Figure 6a for a cell with a 1:6 blend, the value is nevertheless considerably improved compared to that for the archetype CuPc/C₆₀ cell, where $\Delta E_{\rm G} = 1.3$ eV versus $V_{\rm oc} = 0.55$ V^{23} The high V_{oc} in the blended cells is due to their relatively large series resistance, which is clearly apparent in Figure 5, which results in a low FF and a flattening of the J-V characteristics near J = 0. Nevertheless, the $V_{\rm oc}$ of the low series resistance control is 0.79 eV, indicative of reduced recombination (and hence lower dark current) as compared to a conventional CuPc-based cell.^{23–25}

An increase of $PC_{70}BM$ concentration to 1:2, 1:3, and 1:6 increases the formation of electron conducting pathways to the cathode. This also reduces the probability for hole shunts formed by the SQ regions while

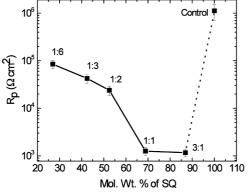


Figure 9. Parallel resistance (R_p) versus the molecular weight ratio between squaraine and PC₇₀BM obtained from fitting the current density characteristics using the modified Shockley Equation (see text) of solar cells shown in Figures 4–7. Also shown is the parallel resistance for the SQ/C₆₀ control cell.

increasing the interfacial area between donor and acceptor regions in the bulk heterojunction. While the surface roughness is relatively high in these mixtures, the improved bulk heterojunction morphology ultimately results in higher efficiencies, even at high illumination intensities. Note also that there is no significant increase of the EQE photoresponse contributed by the SQ donor (Figure 4) at a wavelength of $\lambda = 685$ nm for these bulk cells. In contrast, there is a doubling in the EQE in the wavelength range from $\lambda = 350$ to 600 nm, due to PC₇₀BM absorption. As noted above, the relative balance in magnitude of EQE from both PC₇₀BM and SQ across the wavelength region from 350 to 750 nm compared to the absorption characteristics of these mixtures in Figure 2 indicates that carrier conduction limits the cell response, while the mixtures support very efficient exciton diffusion and dissociation at the high surface area interface between donor and acceptor regions. This observation is supported by the relatively low EQE of the nanocrystalline SQ/C₆₀ control cell, especially at short wavelengths where we expect that exciton dissociation, and not charge collection limits cell performance.

At SQ:PC₇₀BM mixtures of 1:8 or larger, shorts are formed due to continuous conducting paths of this electron acceptor between anode and cathode. This sets an upper bound to the amount of PC₇₀BM that can be used in the bulk heterojunction before it loses its nanoscale network that can efficiently dissociate excitons. Furthermore, none of the mixtures show a crystalline morphology, as indicated by the XRD patterns for thin film blends shown in Figure 1. This lack of crystallinity is primarily responsible for the relatively low mobilities and hence fill factors and power conversion efficiencies at high illumination intensities in these blended cells, in contrast to the homogeneous, planar SQ/C₆₀ control devices.¹⁴

Indeed, the relatively high FF (0.54 \pm 0.02) of the SQ/ C₆₀ planar control cell results from its high hole mobility and hence high charge collection efficiency.²⁶ The lack of a continuous interpenetrating network of SQ domains in the blended cells ultimately limits their performance to less than that of the planar junction.^{27,28} Therefore, further control of the nanoscale morphology and crystallinity in the SQ:PC70BM composites, possibly achieved by employing a higher annealing temperature, is required. Since the power efficiencies of the 1:2 bulk and planar junctions are similar at low intensities even though the EQE of the latter cell is higher, we suggest that modification of the SQ molecules to form such morphologies may ultimately lead to power conversion efficiencies significantly in excess of 4% at high intensities for these solution-processed junctions.

CONCLUSIONS

Using a combination of XRD, AFM, and measurements of hole mobilities in interpenetrating networks

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of SQ and PC₇₀BM, we have demonstrated a series of solution-processed, small-molecule SQ:PC₇₀BM solar cells with various donor-to-acceptor constituent ratios. We find that the 1:2 SQ:PC₇₀BM cells have peak efficiencies at low light levels of 4.1 \pm 0.2% (solar spectral mismatch corrected), which is comparable to that of the control, solution+vacuum deposited planar nanocrystalline SQ/C₆₀ cells (4.1 \pm 0.2%). However, these latter structures maintain their high efficiency even at intensities exceeding 1 sun, AM1.5G simulated solar intensity.

We have shown that the performance of these cells is largely determined by the nanomorphology of the bulk heterojunctions formed during film deposition and subsequent annealing. The roll off in efficiency (which is due to a roll off in FF) at high intensities in the blends, but not observed in the planar junction control cells, arises from the formation of discontinuous pathways for electron and hole transport. However, the blended films have a more uniform and higher EQE than that of the planar device, suggesting that further control of the nanostructure, possibly using a modified SQ molecule with a higher potential for $\pi - \pi$ stacking into a regular, crystalline structure, can result in increased efficiency at high illumination intensities.

EXPERIMENTAL SECTION

X-ray-diffraction (XRD) patterns of the SQ powder plus the neat SQ, PC₇₀BM (American Dye Source, Inc.) and SQ:PC₇₀BM (in weight concentrations of 3:1, 1:1, 1:2, 1:3, and 1:6) thin films spin-coated on indium tin oxide (ITO) substrates at a rate of 3000 rpm (revolutions per minute) were obtained using a Rigaku diffractometer in the $\theta - 2\theta$ geometry using a 40 kV Cu K α radiation source. The neat SQ thin films with thicknesses of 360 Å were annealed at temperatures varied from 70 to 130 °C. The thicknesses of the five blends from 1:3 to 1:6 SQ:PC₇₀BM cast from 20 mg/mL solutions in chloroform, as determined by using Woolam VASE ellipsometer, were 1660, 1530, 720, 730, and 760 Å. The absorption spectra of the pure and blended films on quartz substrates with various compositions were measured using a Perkin-Elmer Lambda 1500 UV-NIR spectrometer.

The ionization potential energy for the SQ thin film was measured by ultraviolet photoemission spectroscopy (UPS) using 21.22 eV He–I emission in a Thermo VG Scientific Clam4MCD analyzer system. Samples were prepared by thermal evaporation onto a p-type Si substrate of a 30 nm thick Au film, followed by a 10 nm thick SQ film. Transfers between the deposition chambers and the analysis chamber were performed at <10⁻⁸ Torr, while the UPS pressure was <10⁻⁹ Torr. The analyzer resolution was ~0.15 eV as determined by a fit to the Fermi level of Au.

Samples for atomic force microscopy (AFM) operated in the tapping mode were prepared by first casting SQ:PC₇₀BM blend thin films on ITO-coated glass substrates with an 80 Å thick molybdenum oxide (MoO₃) film predeposited on its surface by thermal evaporation. The films were annealed at 70 °C for 10 min in a N₂ glovebox.

The active layers of the PV cells consisted of SQ in PC₇₀BM blends prepared from totally dissolved solids in chloroform in air. The weight ratios of SQ to PC₇₀BM were varied as in the case of the XRD samples. The separate solutions of SQ and PC₇₀BM were first stirred at room temperature for 12 h before the solutions were mixed to form the blends, which were then stirred for 2 h and used to spin-coat the active layers at rates ranging from 1000 rpm to 6000 rpm for 30 s.

Devices were fabricated as follows: The ITO-coated glass substrate was precleaned with organic solvents and exposed to ultraviolet/ozone following procedures described elsewhere.^{10,15} Measurements of thin film hole mobility used the following sandwich structures: ITO/poly(3,4-ethylenedioxythiphene) poly-(styrenesulfonate) (PEDOT:PSS) (460 Å)/SQ(360 Å)/Au (1000 Å) and ITO/PEDOT:PSS(460 Å)/SQ:PC70BM/Au (1000 Å). Solar cells employed the following structure: ITO/MoO₃(80 Å)/SQ:PC₇₀BM(x Å)/Al(1000 Å). Here, MoO₃ is thermally evaporated onto the ITO surface in a vacuum system with a base pressure of 10^{-7} Torr. Solutions containing a mixture of SQ:PC70BM (3:1 and 1:1) with a concentration of 10 mg/mL, and SQ:PC₇₀BM (1:2, 1:3, and 1:6) with 20 mg/mL in chloroform were cast on the MoO₃. The films with thicknesses of 320, 400, 720, 730, and 760 Å were then annealed at 70 °C for 10 min in an ultrahigh purity N2 ambient. The devices were completed by thermally evaporating a 1000 Å thick AI cathode through a shadow mask resulting in a device

area of 7.9×10^{-3} cm². For comparison, we also fabricated a 1:6 SQ:PC₆₀BM cell with the same structure as the analogous SQ: PC₇₀BM device.

Using similar procedures, control SQ/C₆₀ and SQ/C₇₀ planar cells were fabricated with the following structure: ITO/MoO₃(80 Å)/SQ(62 Å)/fullerene(400 Å)/bathocuproine (BCP)(100 Å)/Al(1000 Å). The SQ thin film in this case was spin-coated from 1 mg/mL SQ solution in dichloromethane at a rate of 3000 rpm for 30 s, followed by annealing at 110 °C for 10 min.

The current density—voltage (*J*–*V*) characteristics and η_p of the devices were measured using an Oriel 150 W solar simulator irradiation from a Xe arc lamp with AM1.5G filters and an NREL-calibrated standard Si detector. Measurements and solar spectral correction were made using standard methods.²⁹ The EQE was measured using monochromated light from a Xe-lamp, chopped at 400 Hz, and focused to the device active area.

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